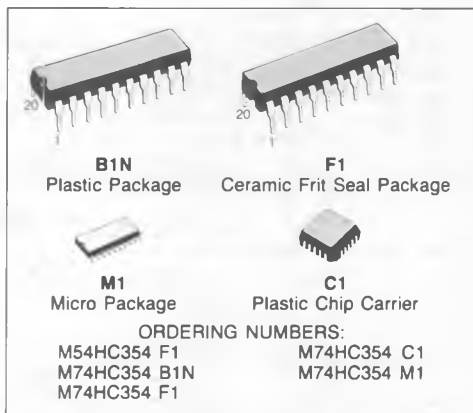


8-CHANNEL MULTIPLEXER/REGISTER (3-STATE)

- **HIGH SPEED**
 $t_{PD} = 33 \text{ ns (TYP.) at } V_{CC} = 5V$
- **LOW POWER DISSIPATION**
 $I_{CC} = 4 \mu A \text{ (MAX.) at } T_A = 25^\circ C$
- **HIGH NOISE IMMUNITY**
 $V_{NIH} = V_{NIL} = 28\% V_{CC} \text{ (MIN.)}$
- **OUTPUT DRIVE CAPABILITY**
 15 LSTTL LOADS
- **SYMMETRICAL OUTPUT IMPEDANCE**
 $|I_{OH}| = I_{OL} = 6 \text{ mA (MIN.)}$
- **BALANCED PROPAGATION DELAYS**
 $t_{PLH} = t_{PHL}$
- **WIDE OPERATING VOLTAGE RANGE**
 $V_{CC} \text{ (OPR.)} = 2V \text{ to } 6V$
- **PIN AND FUNCTION COMPATIBLE**
 WITH 54/74LS354



DESCRIPTION

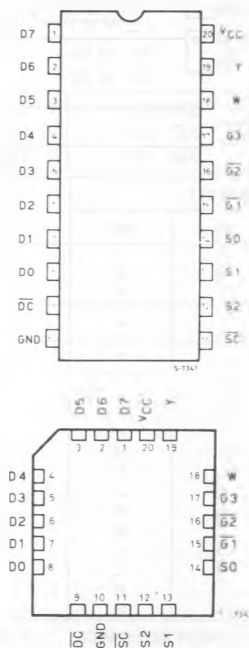
The M54/74HC354 is a high speed CMOS 8-CHANNEL MULTIPLEXER/REGISTER (3-state) fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low consumption.

This device contains an 8 channel digital multiplexer with an 8-bit input data register and a 3-bit address input register with 3-state outputs. The one of eight input data will be provided on the Y output pin (non-inverted output) and W output pin (inverted output) determined by the address data.

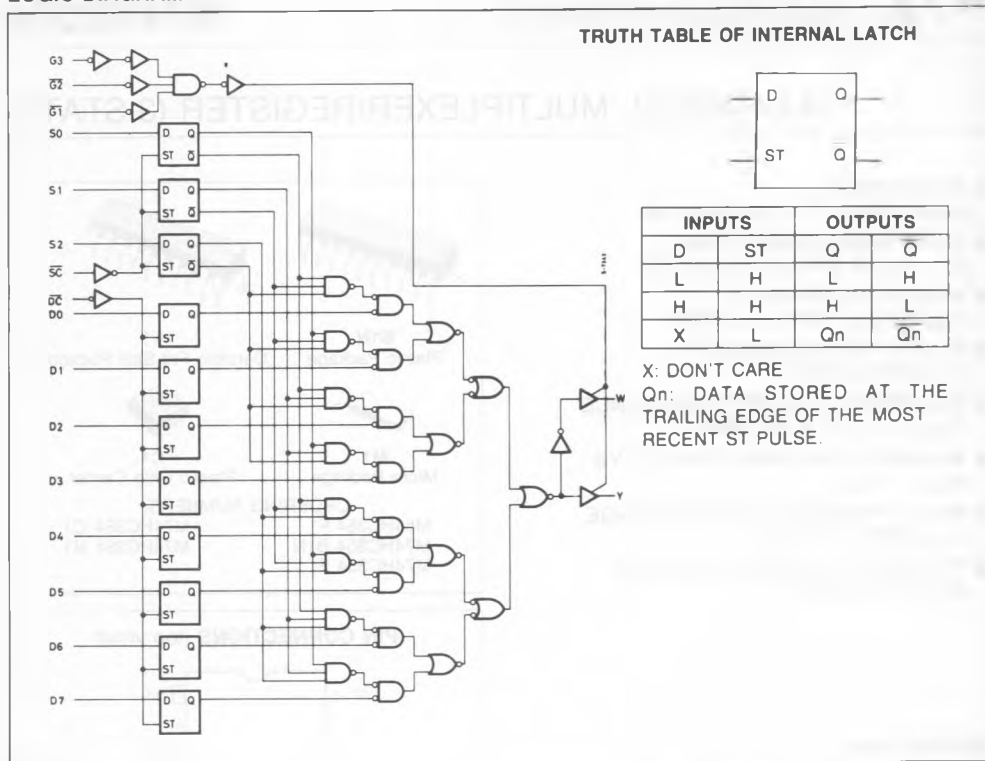
The information at the data inputs (D0 to D7) is stored in the 8-bit latch at the negative pulse on $\overline{DC}$ input. The information at the address inputs (S0 to S2) is stored in the 3-bit latch at the negative pulse on $\overline{SC}$ input. These outputs are disabled to be high-impedance when input $\overline{G1}$ is held high, input $\overline{G2}$ is held high or input $\overline{G3}$ is held low. This device is suitable for interfacing with bus lines in a bus organized system.

The M54/74HC354 is similar in function to the M54/74HC356, which has an 8-bit flip-flop as the data register instead of an 8-bit latch. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTIONS (top view)



LOGIC DIAGRAM



TRUTH TABLE

SELECT*			INPUTS				OUTPUTS	
S2 S1 S0			$\overline{DC}$	OUTPUT ENABLES			W	Y
				G1	G2	G3		
X X X X	X X X X	X X X X	X X X X	H X X X	X H X X	X X L L	Z Z Z Z	Z Z Z Z
L	L	L	L	L	L	H	D_0	D0
L	L	L	H	L	L	H	D_{0n}	D0n
L	L	L	L	L	L	H	D_1	D1
L	L	L	H	L	L	H	D_{1n}	D1n
L	L	L	L	L	L	H	D_2	D2
L	L	L	H	L	L	H	D_{2n}	D2n
L	L	L	L	L	L	H	D_3	D3
L	L	L	H	L	L	H	D_{3n}	D3n
L	L	L	L	L	L	H	D_4	D4
L	L	L	H	L	L	H	D_{4n}	D4n
L	L	L	L	L	L	H	D_5	D5
L	L	L	H	L	L	H	D_{5n}	D5n
L	L	L	L	L	L	H	D_6	D6
L	L	L	H	L	L	H	D_{6n}	D6n
L	L	L	L	L	L	H	D_7	D7
L	L	L	H	L	L	H	D_{7n}	D7n

X: DON'T CARE - Z: HIGH IMPEDANCE

*: THIS COLUMN SHOWS THE INPUT ADDRESS SETUP WITH $\overline{SC}$ LOW.

$D_{0n} \dots D_{7n}$: THE LEVEL OF STEADY-STATE INPUTS AT INPUT D0 THROUGH D7, RESPECTIVELY, BEFORE THE MOST RECENT OF THE LOW-TO-HIGH TRANSITION OF DATA CONTROL.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	− 0.5 to 7	V
V _I	DC Input Voltage	− 0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	− 0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 35	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 70	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	− 65 to 150	°C

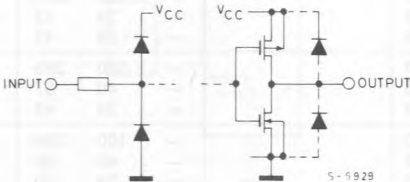
Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≡ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 6	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _A	Operating Temperature 74HC Series 54HC Series	− 40 to 85 − 55 to 125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} { 2 V 0 to 1000 4.5V 0 to 500 6 V 0 to 400	ns

INPUT AND OUTPUT EQUIVALENT CIRCUIT



DC SPECIFICATIONS

Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	2.0 4.5 6.0		1.5 3.15 4.2	— — —	— — —	1.5 3.15 4.2	— — —	1.5 3.15 4.2	— — —	V
V _{IL}	Low Level Input Voltage	2.0 4.5 6.0		— — —	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	V
V _{OH}	High Level Output Voltage	2.0	V _I	1.9	2.0	—	1.9	—	1.9	—	V
		4.5	V _{IH} or V _{IL}	4.4	4.5	—	4.4	—	4.4	—	
		6.0		5.9	6.0	—	5.9	—	5.9	—	
V _{OL}	Low Level Output Voltage	2.0		4.18	4.31	—	4.13	—	4.10	—	V
		4.5		5.68	5.8	—	5.63	—	5.60	—	
		6.0		—	—	—	—	—	—	—	
V _{OL}	Low Level Output Voltage	2.0	V _{IH} or V _{IL}	—	0.0	0.1	—	0.1	—	0.1	V
		4.5		—	0.0	0.1	—	0.1	—	0.1	
		6.0		—	0.0	0.1	—	0.1	—	0.1	
V _{OL}	Low Level Output Voltage	2.0		—	0.17	0.26	—	0.33	—	0.40	V
		4.5		—	0.18	0.26	—	0.33	—	0.40	
		6.0		—	—	—	—	—	—	—	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND	—	—	±0.1	—	±1.0	—	±1.0	μA
I _{OZ}	3 State Output Off-State Current	6.0	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND	—	—	±0.5	—	±5	—	±10	μA
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND	—	—	4	—	40	—	80	μA

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input t_r = t_f = 6ns)

Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0 4.5 6.0		— — —	25 7 6	60 12 10	— — —	75 15 13	— — —	90 18 15	ns
t _{PLH} t _{PHL}	Propagation Delay Time (Dn - Y, W)	2.0 4.5 6.0		— — —	135 34 29	260 52 44	— — —	325 65 55	— — —	390 78 66	ns
t _{PLH} t _{PHL}	Propagation Delay Time (DC - Y, W)	2.0 4.5 6.0		— — —	135 34 29	265 53 45	— — —	335 66 56	— — —	400 80 68	ns
t _{PLH} t _{PHL}	Propagation Delay Time (Sn-Y, W)	2.0 4.5 6.0		— — —	160 40 34	285 57 48	— — —	355 71 60	— — —	430 86 73	ns
t _{PLH} t _{PHL}	Propagation Delay Time (SC-Y, N)	2.0 4.5 6.0		— — —	160 40 34	295 59 50	— — —	370 74 63	— — —	445 89 76	ns
t _{W(L)}	Minimum Pulse Width (DC)	2.0 4.5 6.0		— — —	30 8 7	75 15 13	— — —	95 19 16	— — —	110 22 19	ns

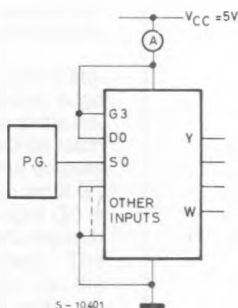
AC ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	V _{CC}	Test Condition	T _A = 25°C 54HC and 74HC			- 40 to 85°C 74HC		- 55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{W(L)}	Minimum Pulse Width (SC)	2.0		—	30	75	—	95		110	ns
		4.5		—	8	15	—	19		22	
		6.0		—	7	13	—	16		19	
t _s	Minimum Set-up Time (Sn)	2.0		—	20	75	—	95		110	ns
		4.5		—	5	15	—	19		22	
		6.0		—	4	13	—	16		19	
t _s	Minimum Set-up Time (Dn)	2.0		—	25	75	—	95	—	110	ns
		4.5		—	5	15	—	19	—	22	
		6.0		—	4	13	—	16	—	19	
t _h	Minimum Hold Time (Sn)	2.0		—	—	5	—	5		5	ns
		4.5		—	—	5	—	5		5	
		6.0		—	—	5	—	5	—	5	
t _h	Minimum Hold Time (Dn)	2.0		—	—	0	—	0	—	0	ns
		4.5		—	—	0	—	0	—	0	
		6.0		—	—	0	—	0	—	0	
t _{PZL} t _{PZH}	Output Enable Time	2.0	R _L = 1kΩ	—	68	125	—	155		190	
		4.5		—	17	25	—	31		38	
		6.0		—	15	21	—	26		32	
t _{PLZ} t _{PHZ}	Output Disable Time	2.0	R _L = 1kΩ	—	60	155	—	195		235	ns
		4.5		—	22	31	—	39		47	
		6.0		—	20	26	—	33		40	
C _{IN}	Input Capacitance			—	5	10	—	10		10	
C _{OUT}	Output Capacitance			—	10	—	—	—			pF
C _{PD} (*)	Power Dissipation Capacitance			—	84	—	—	—			pF

Note (*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit)

Average operating current can be obtained by the following equation.

$$I_{CC}(\text{Opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

TEST CIRCUIT I_{CC} (Opr.)

INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST

SWITCHING CHARACTERISTICS TEST WAVEFORM

